Reversing of humidity response of MoS₂- and WS₂-based sensors with metal coatings

Peng Xiao^{1,2}, Christopher Hardly Joseph^{4,5}, Emigdio Chavez-Angel¹, Antonino Cataldo^{4,5} Davide Mencarelli^{4,5}, Luca Pierantoni^{4,5}, Clivia M. Sotomayor Torres^{1,3} and Marianna Sledzinska¹

¹Catalan Institute of Nanoscience and Nanotechnology (ICN2), CSIC and BIST, Campus UAB, Bellaterra, 08193 Barcelona, Spain

² Departamento de Física, Universidad Autónoma de Barcelona, Bellaterra, E-08193 Barcelona, Spain
³ICREA, Pg. Lluís Companys 23, 08010 Barcelona, Spain

⁴Department of Information Engineering, Polytechnic University of Marche, Via Brecce Bianche, 1, 60131 Ancona, Italy

⁵INFN-Laboratori Nazionali di Frascati, via E. Fermi 40, 00044 Frascati, Italy

Abstract

Two-dimensional materials, such as transition metal dichalcogenides, have been identified as attractive candidates for sensing applications due to their high surface-to-volume ratio, chemically active edges and good electrical performance. However, their electrical response to humidity is still under debate and the experimental reports still remain inconclusive. For instance, the impedance of the MoS₂-based sensors decreases or increases with increasing humidity, compromising the use of MoS₂ for humidity sensing. In this work we focus on understanding the interaction between water and the transition metal dichalcogenides. We fabricated and studied humidity sensors based on MoS₂ and WS₂ coated with copper and silver metals. The devices exhibited high chemical stability and excellent humidity sensing performance in relative humidity between 4 and 80%, with response and recovery times of 2 and 40 seconds, respectively. We have systematically investigated the humidity response of the materials as a function of the type and amount of metal coating and observed the reverse action of sensing mechanisms. This phenomenon is explained based on a detailed structural analysis of the samples considering the Grotthuss mechanism in the presence of charge trapping, which was verified by simulations of an appropriate lumped-element model. Our findings open up a possibility for tuning of the electrical response in a facile manner and without compromising the high performance of our sensor.